

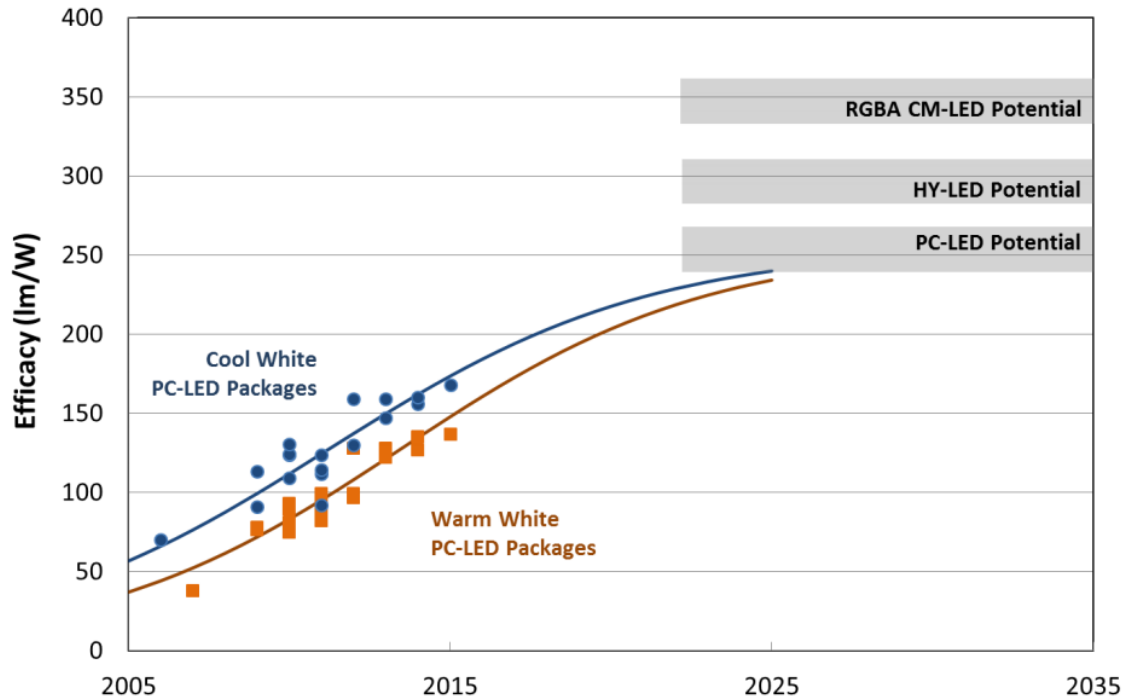
LED technology considerations for high luminance sources

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Device Architecture
LUMILEDS, San Jose CA, USA

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Tremendous progress in LED efficiency

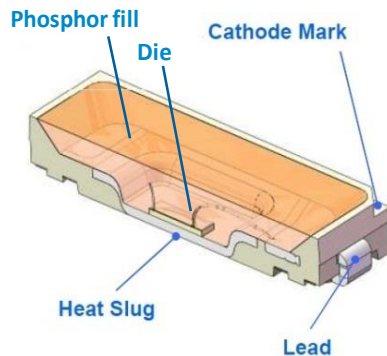


Note: Blue = cool white (5700K) data (circles) and logistic fit (line); orange = warm white (3000K) data (squares) and logistic fit (line). Late-2015 measured commercial products reach approximately 160 lm/W for cool white and approximately 140 lm/W for warm white. Approximate long-term-future potential efficacies of three white-light architectures (pc-LED, hy-LED, RGBA cm-LED) are shown as grey bars.

Figure 5.4: Efficacies of Commercial LED Packages Measured at 25°C and 35 A/cm² Input Current Density

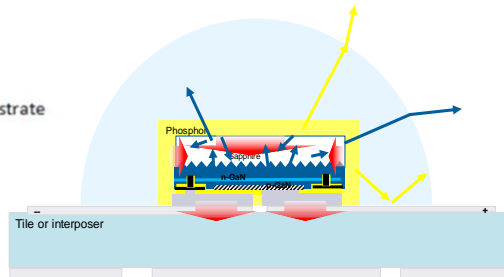
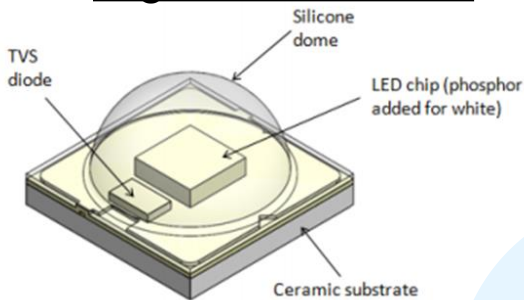
Dominant high efficiency architectures

Mid-Power LEDs



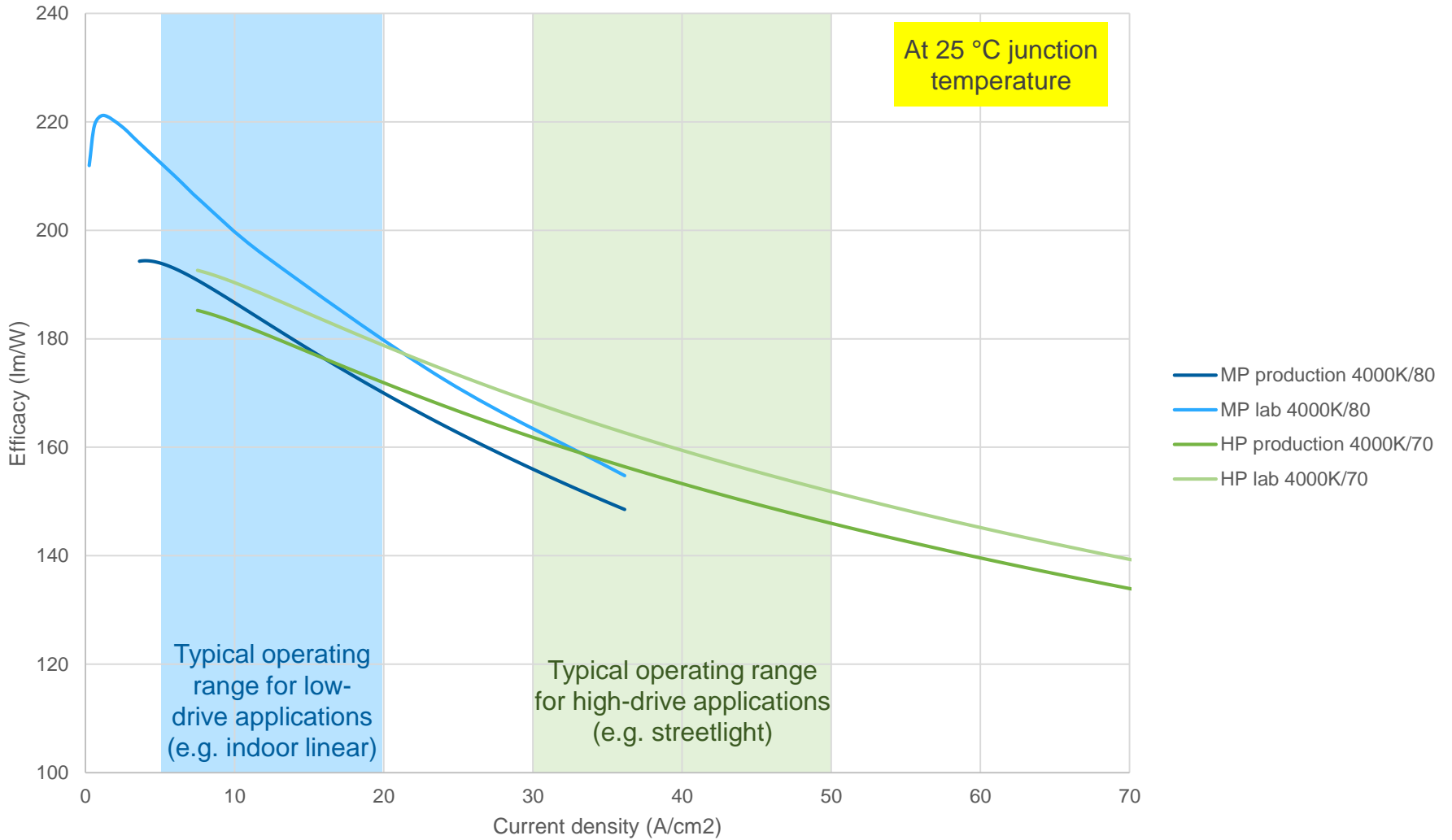
- High extraction efficiency die
- Low operating power densities allow for high epi IQE
- Large highly reflective cup reduces optical losses
- Large volume of phosphor relative to die area reduces irradiance levels: lower photoquenching and high package efficiency

High-Power LEDs



- High extraction Thin-Film or Flip-Chip die
- Highly reflective and thermally conductive submount
- Flip-Chip die allows for reduction in photo-thermal quenching of phosphors
- Die footprint 2mm^2 or larger to keep epi IQE high
- Large silicone dome to aid photon extraction

LEDs for low-drive vs. high-drive applications



Etendue and brightness limitations of dominant high efficiency architectures

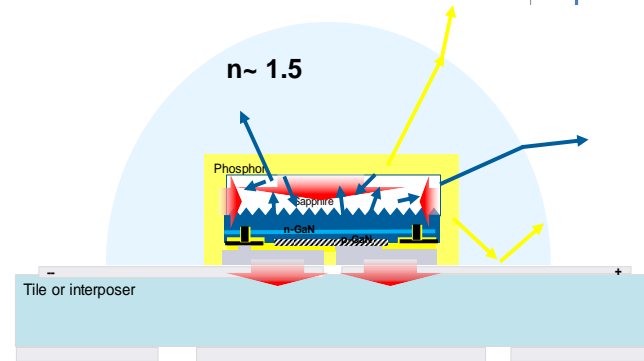
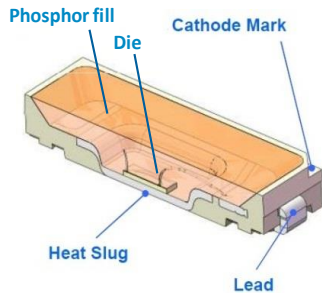
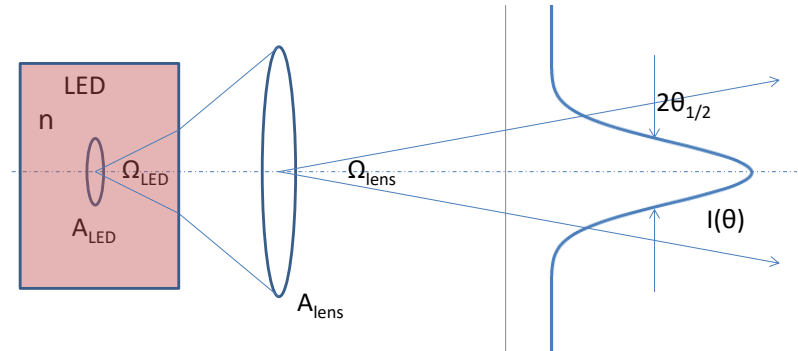
Etendue $G = n^2 \cdot A \cdot \Omega$,

Where A is the area of the emitting source

Ω is the emission solid angle

n is the index of refraction

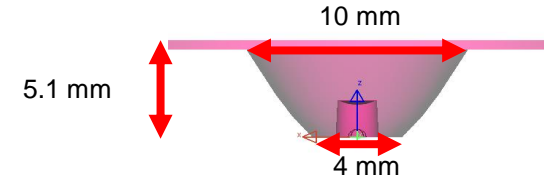
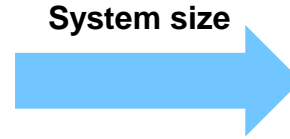
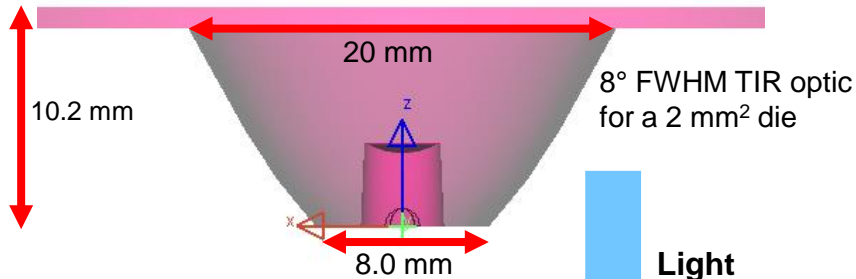
Etendue can only increase in an optical system (optical equivalent of Entropy)



- Large source area
 - increases etendue
- Input power limited by:
 - die design
 - die attach

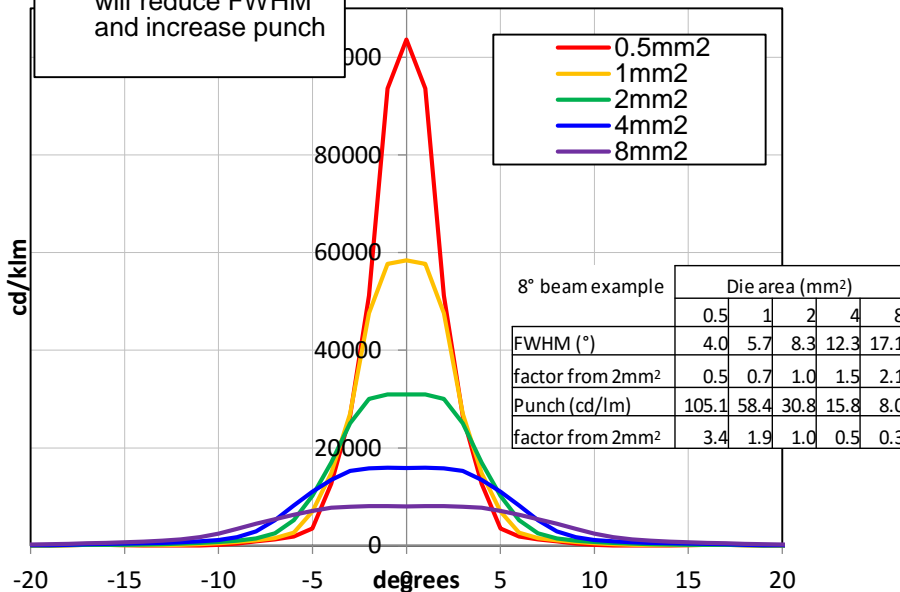
- Common die footprint 1-2mm² or larger
 - increases etendue
- Silicone dome
 - increases etendue
- Multi-side emitters: larger solid angle
 - increases etendue

Versatility of low etendue, high brightness sources



Still using an 8° FWHM TIR optic, going to a 0.5 mm² die, reduces x, y and z by a factor of 2: 8x system volume reduction

- Beam profiles for various die areas using the same optic
- Smaller source size will reduce FWHM and increase punch

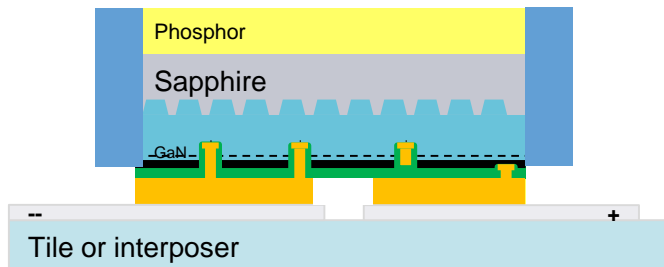


-We illustrate system level impact of source etendue by varying source area

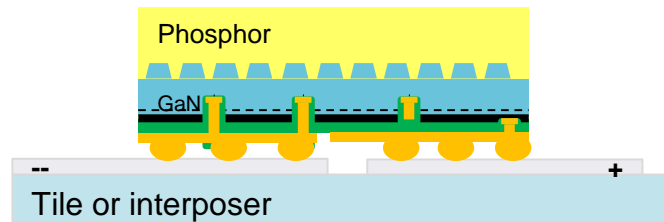
-Lower source etendue allows greater freedom to optimize for light utilization and system size

High-luminance LED architectures

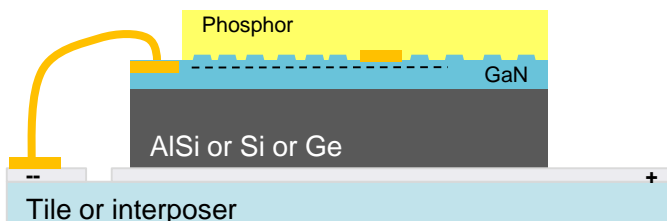
Chip-Scale Package (CSP)



Thin-Film Flip-chip (TFFC)

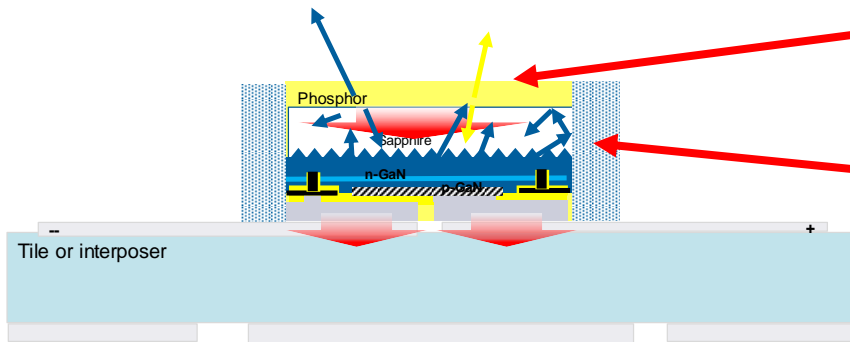


Vertical Thin-Film (VTF)

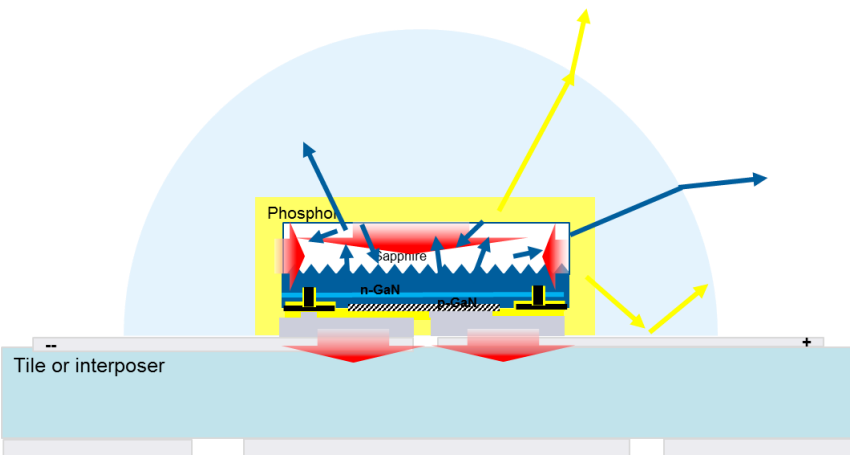


- **Key features of low-extended, high-luminance architectures:**
 - Small source size
 - High current density die
 - Low thermal resistance
 - Proximity “on-chip” phosphor
 - Single-sided emitter (side-coated phosphor and die as needed)
 - No dome
- **Challenges:**
 - Lower optical Package Efficiency due to absence of dome and the addition of side-coat
 - With current densities above 35A/cm² need to consider:
 - impact of EPI IQE droop
 - impact phosphor photo-thermal quenching

Package efficiency penalty for high luminance architectures



- Reduced extraction with removal of domes
- Reduced extraction of photons with side-coat
- Due to finite thickness of converters need side-coat even with Thin-Film architectures
- Reduced phosphor heat dissipation and higher photo-quenching compared to multi-side emitters



Key focus area: optical absorption in the pump chip

Phosphor droop in LEDs

- For this example of a typical warm white pcLED,
 - the PCE relative drop is ~4% for each doubling of blue light power density
 - This drop accounts for 20-25% of the total white LED efficiency droop with drive

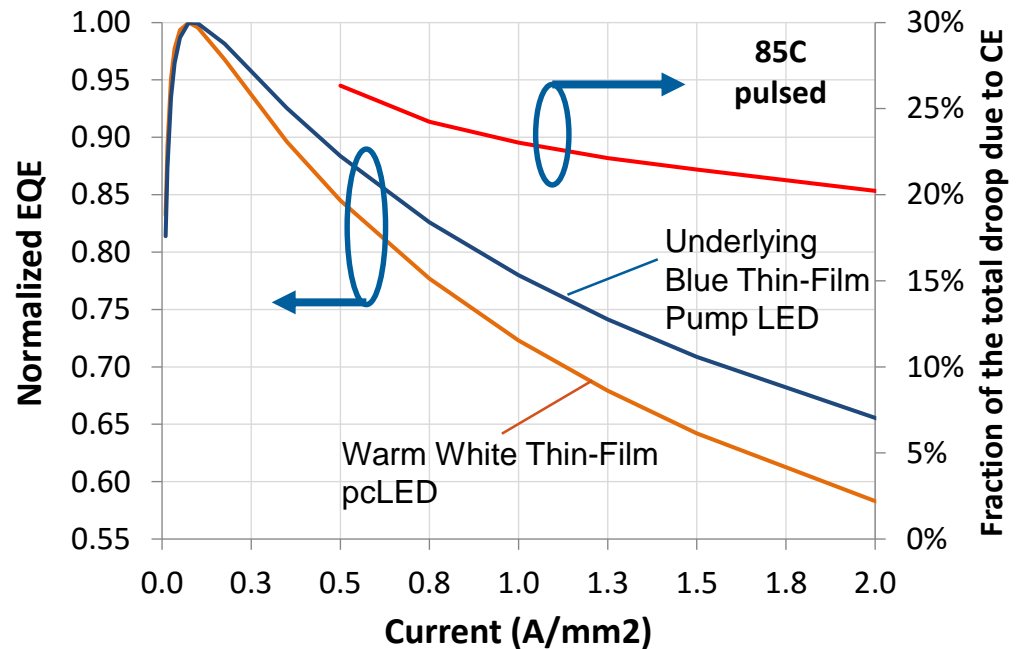
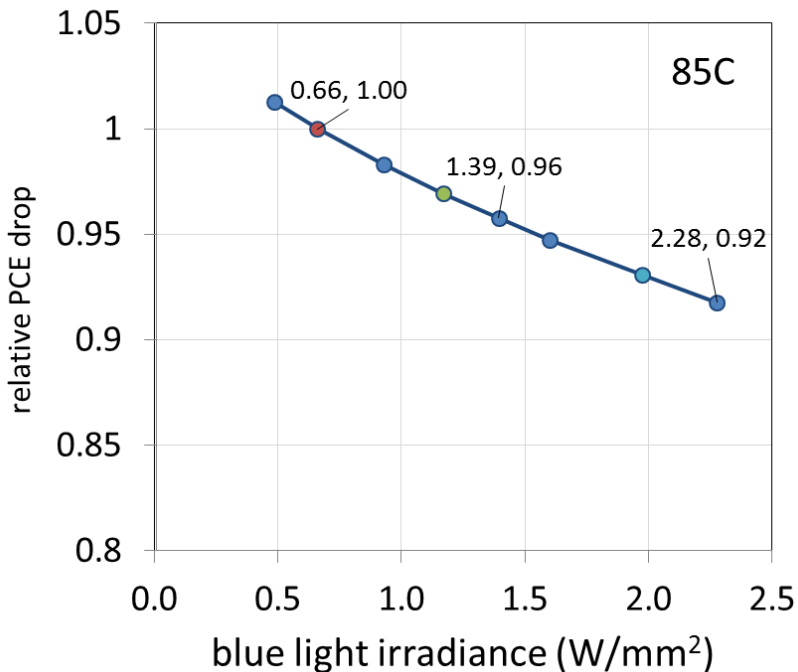
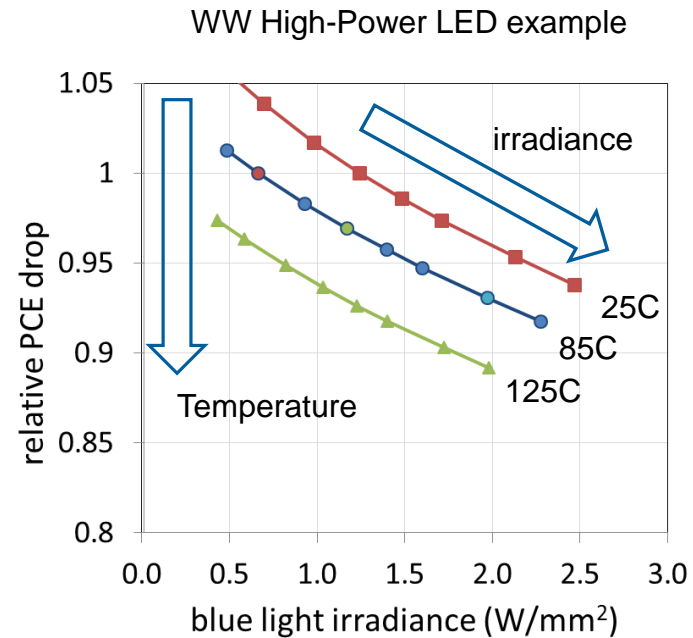
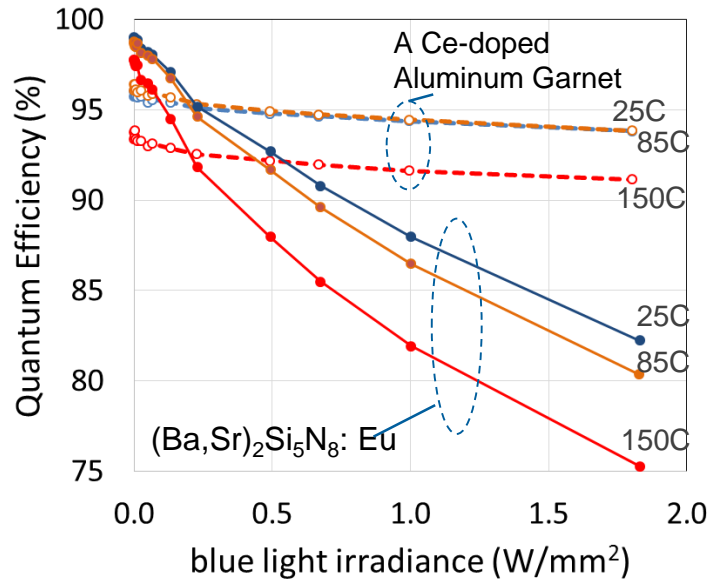
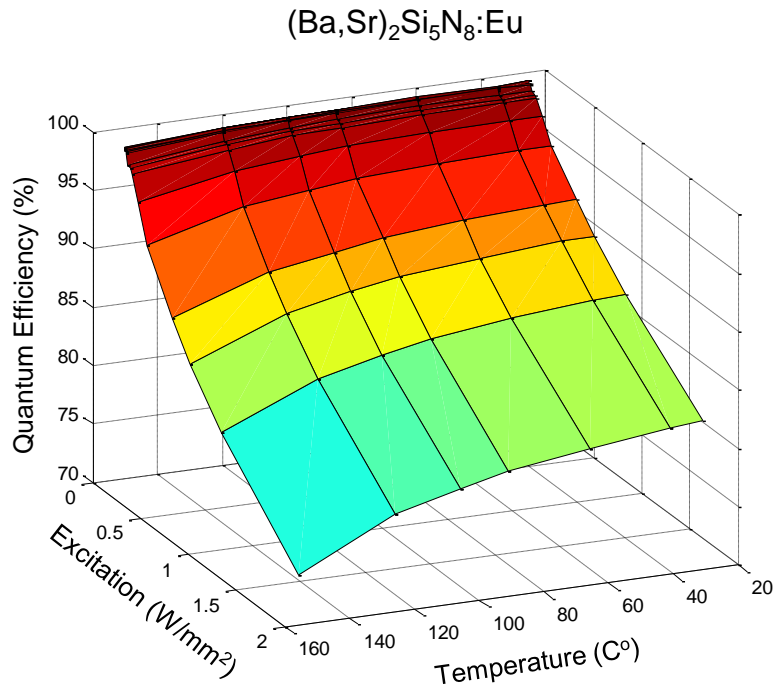


Photo-thermal quenching of phosphors in LEDs: impact on conversion efficiency

- Photo-quenching in Eu^{2+} red nitrides shows strong dependence on temperature
- Cerium-doped aluminum garnets show little dependence of photo-quenching on temperature, but, depending on composition, may exhibit considerable thermal quenching
- Photo-thermal quenching of phosphors readily translates into Conversion Efficiency (CE) quenching in pcLEDs
- At typical operating conditions of a HP LED $T_{\text{phosphor}} > 100\text{C}$, irradiance $0.7 - 1.5 \text{ W/mm}^2$



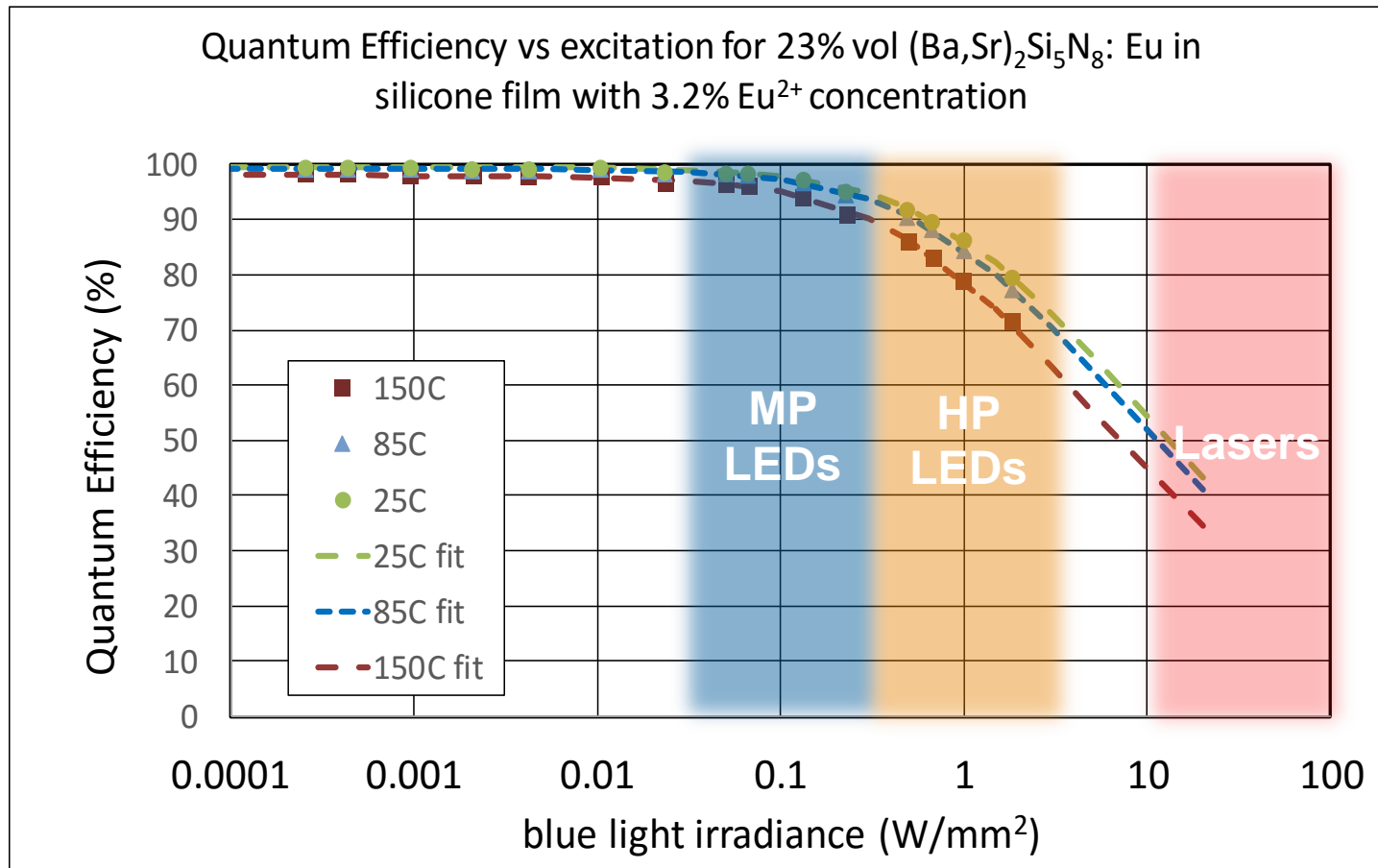
Dependence of phosphor droop on temperature: Photo-Thermal Quenching



- Photo-quenching in Eu²⁺ red nitrides shows strong dependence on temperature
- Thermal quenching is rather low at low excitation where QE measurements are usually done and quoted
- Thermal and photo effects on QE need to be considered in LEDs

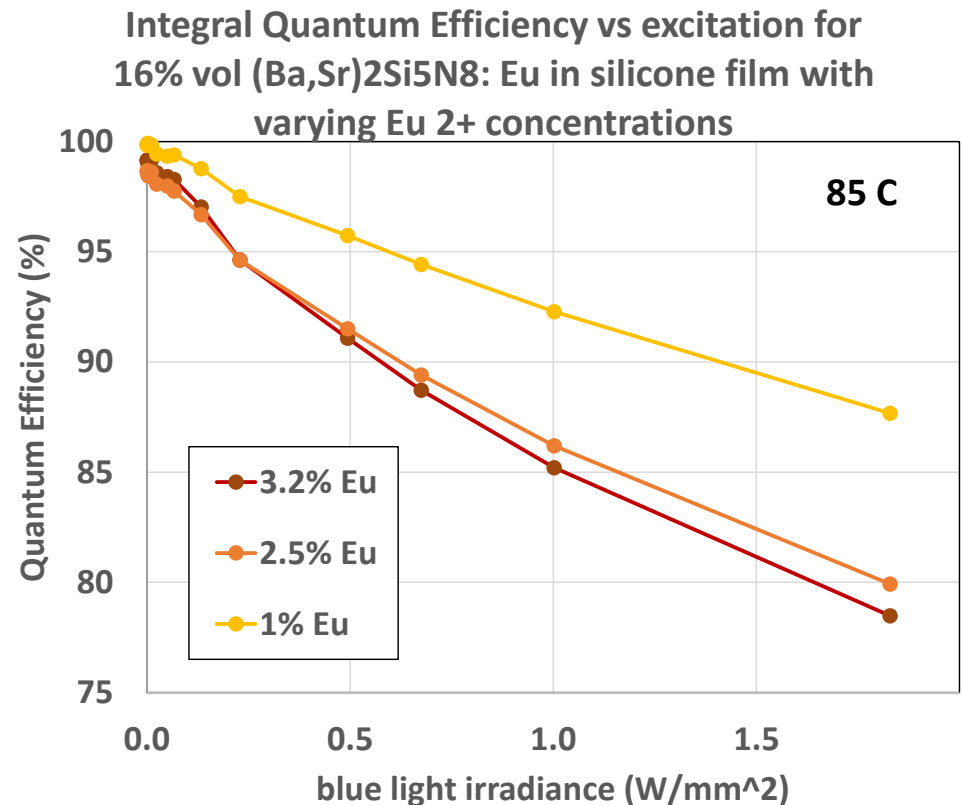
(Ba,Sr)₂Si₅N₈: Eu powder phosphor doped with 2.5% Eu²⁺ in a film of silicone

Example of phosphor QE in different applications



Droop dependence on activator concentration

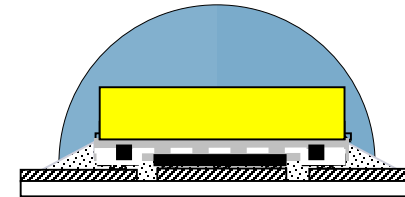
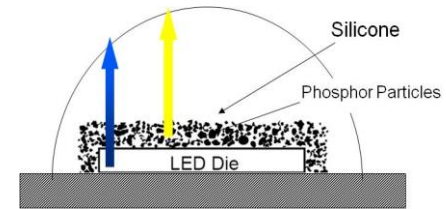
- Photo-quenching in Eu^{2+} red nitrides shows strong dependence on activator concentration
- Red nitride phosphors with higher Eu^{2+} concentration are used for high CRI applications
- Conversion efficiency droop due to PTQ is most pronounced for warm white, high Ra emitters



Adapted from: Oleg B. Shchekin et al, Phys. Status Solidi RRL, 1–5 (2016) / DOI 10.1002/pssr.201600006

Converter materials for high-power density operation

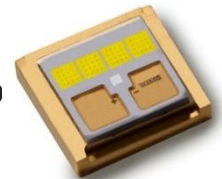
- Keep activator concentration in the phosphor low to minimize PTQ
- Maximize heat conductivity through the converting layer and out
- Low activator concentration in powder phosphors leads to increased phosphor layer thickness or loading to achieve a target color point. This results in:
 - Efficiency penalty due to excessive scattering
 - Efficiency penalty due to poor thermals of the thicker layer
- In a ceramic phosphor, scattering can be tightly controlled to allow for thicker layers enabling lower activator concentration
- High thermal conductivity of ceramic allows for flexibility in phosphor thickness
- Ceramic phosphors are well suited for high power density applications



Lumileds Lumiramic
(ceramic phosphor)
technology examples in high
power density applications



LUXEON F PC Amb



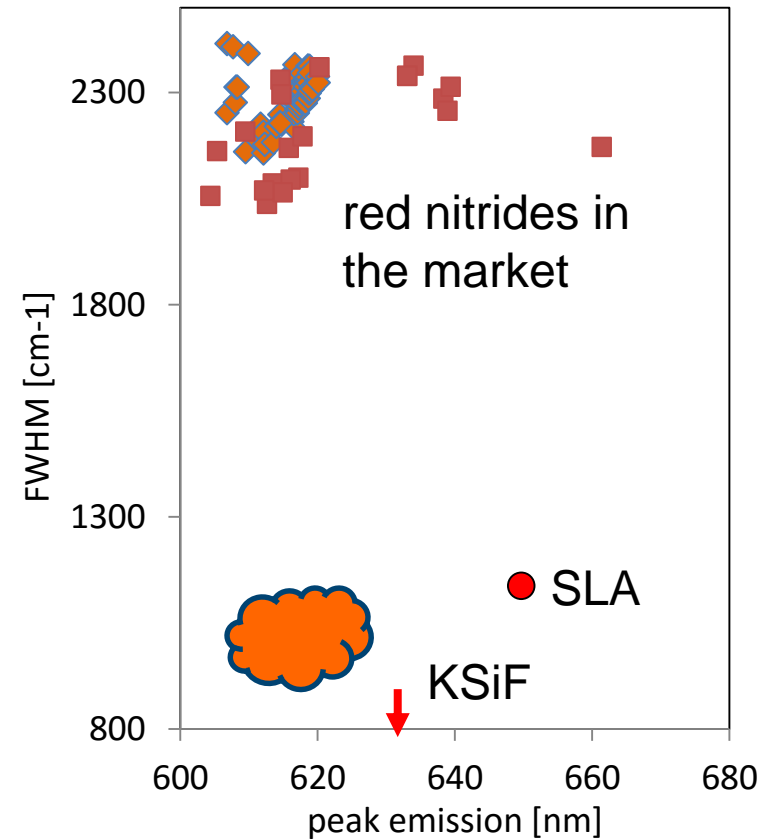
LUXEON Altilon H1K

Gains in conversion efficiency from phosphor emission linewidth

CE vs phosphor FWHM with optimum peak wavelength; 3000K, 80 CRI

		Green FWHM					
		30	50	70	90	110	130
Red FWHM	CE	30	50	70	90	110	130
	30	24%					
	50						
	70						
	90				0%	0%	
	110					-7%	

- Other than QDs, don't yet have a phosphor material allowing full freedom in spectral engineering



Status of red phosphors for high luminance applications

	FWHM	WL	QE low drive	QE high drive
Eu ²⁺ 258 and SCASN nitrides	Red	Green	Green	Red
SLA	Green	Yellow	Green	Yellow
KSIF	Green	Yellow	Green	Red
QDs	Green	Green	Green	Red

- Don't have materials fulfilling all the requirements; fundamental materials development needed
- Focus needed on PTQ and QE at operating conditions in addition to spectral characteristics

Summary

- High luminance LEDs can enable significant value add from system form factor, weight and cost reductions.
- Developing efficient high-luminance LEDs requires improvement in
 - epi droop
 - die design for high power densities
 - Die and package technologies for high photon extraction
 - Low droop phosphors for WW and high Ra

